

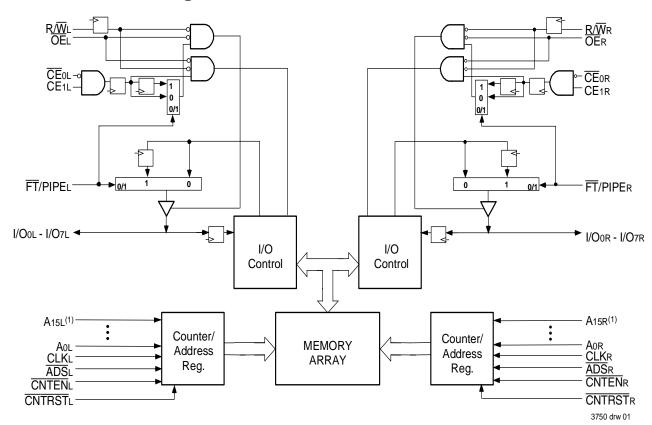
IDT70V9089/79S/L

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 6.5/7.5/9/12/15ns (max.)
 - Industrial: 9ns (max.)
- Low-power operation
 - IDT70V9089/79S Active: 429mW (typ.) Standby: 3.3mW (typ.)
 - IDT70V9089/79L Active: 429mW (typ.) Standby: 660mW (typ.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pin

- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 4ns setup to clock and 1ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 6.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 10ns cycle time, 100MHz operation in the Pipelined output mode
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100 pin Thin Quad Flatpack (TQFP) package

Functional Block Diagram



NOTE:

1. A₁₅x is a NC for ID70V9079.

MAY 2004

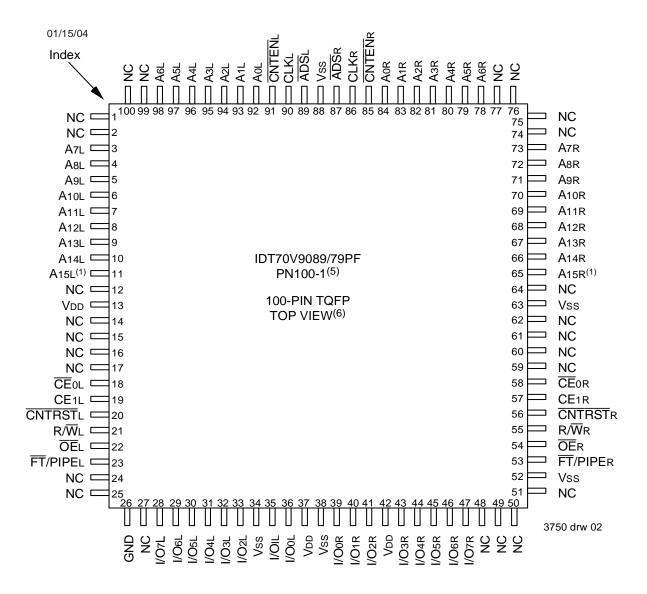
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Description:

The IDT70V9089/79 is a high-speed 64/32K x 8 bit synNchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9089/79 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}_0$ and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 429mW of power.

Pin Configurations (2,3,4)



- 1. A₁₅x is a NC for ID70V9079.
- 2. All Vcc pins must be connected to power supply.
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names		
CEOL, CE1L	CEOR, CE1R	Chip Enables		
$R/\overline{W}L$	R/WR	Read/Write Enable		
ŌĒL	ŌĒR	Output Enable		
A0L - A15L ⁽¹⁾	A0R - A15R ⁽¹⁾	Address		
I/O0L - I/O7L	I/O0R - I/O7R	Data Input/Output		
CLKL	CLKR	Clock		
ADSL	ĀDSR	Address Strobe		
CNTENL	CNTENR	Counter Enable		
CNTRSTL	CNTRSTR	Counter Reset		
FT/PIPEL	FT/PIPER	Flow-Through/Pipeline		
V	DD	Power (3.3V)		
V	SS	Ground (0V)		

3750 tbl 01

NOTE:

- 1. A15x is a NC for ID70V9079.
- 2. $\overline{\text{LB}}$ and $\overline{\text{UB}}$ are single buffered regardless of state of $\overline{\text{FT}}/\text{PIPE}$.
- CEo and CE1 are single buffered when FT/PIPE = VIL, CEo and CE1 are double buffered when FT/PIPE = VIH, i.e. the signals take two cycles to deselect.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	<u>CE</u> ₀	CE ₁	R/W	I/O ₀₋₇	Mode
Х	↑	Н	Χ	Х	High-Z	Deselected - Power Down
Х	↑	Х	L	Х	High-Z	Deselected - Power Down
Х	↑	L	Н	L	DATAIN	Write
L	↑	L	Н	Н	DATAout	Read
Н	Х	L	Н	Х	High-Z	Outputs Disabled

3750 tbl 02

NOTES:

- 1. "H" = V_{IH} , "L" = V_{IL} , "X" = Don't Care.
- 2. \overline{ADS} , \overline{CNTEN} , $\overline{CNTRST} = X$.
- 3. $\overline{\text{OE}}$ is an asynchronous input signal.

Truth Table II—Address Counter Control^(1,2,3)

						<u> </u>						
External Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE				
An	Х	An	1	L ⁽⁴⁾	Х	Н	Di/o (n)	External Address Used				
Х	An	An + 1	↑	Н	L ⁽⁵⁾	Н	Dvo(n+1)	Counter Enabled—Internal Address generation				
Х	An + 1	An + 1	1	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)				
Х	Х	A0	1	Х	Х	L ⁽⁴⁾	DI/O(0)	Counter Reset to Address 0				

3750 tbl 03

- 1. "H" = V_{IH}, "L" = V_{IL}, "X" = Don't Care.
- 2. \overline{CE}_0 and \overline{OE} = V_{IL}; CE₁ and R/ \overline{W} = V_{IH}.
- 3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. ADS and CNTRST are independent of all other signals including CEo and CE1.
- 5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CEo and CE1.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	VDD
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

3750 tbl 04

NOTES

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
V _{DD}	Supply Voltage	3.0	3.3	3.6	٧
Vss	Ground	0	0	0	٧
VIH	Input High Voltage	2.2	_	VDD + 0.3V ⁽¹⁾	٧
VIL	Input Low Voltage	-0.3 ⁽²⁾		0.8	٧

3750 thl 05

NOTES:

- 1. VTERM must not exceed VDD +0.3V.
- 2. $VIL \ge -1.5V$ for pulse width less than 10ns.

Absolute Maximum Ratings(1)

ABSOIGE	<u>e maxiillalli r</u>	latiliyə 🔧	
Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	٧
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	۰C
TJN	Junction Temperature	+150	۰C
Іоит	DC Output Current	50	mA

3750 tb1 06

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed VDD +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 0.3V.
- 3. Ambient Temperature Under Bias. Chip Deselected.

Capacitance (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

3750 tbl 07

- These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 0.3V)

			70V9089/79S		70V90		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	V _{DD} = 3.3V, V _{IN} = 0V to V _{DD}	-	10	-	5	μA
lLO	Output Leakage Current	$\overline{\text{CE}}_0$ = ViH or CE1 = ViL, VouT = 0V to VDD	ı	10	ı	5	μA
Vol	Output Low Voltage	IoL = +4mA	_	0.4	ı	0.4	V
Vон	Output High Voltage	Iон = -4mA	2.4		2.4	_	V

NOTE:

3750 tbl 08

DC Electrical Characteristics Over the Operating
Temperature and Supply Voltage Range⁽⁶⁾ (VDD = 3.3V ± 0.3V)

ICIIIP	ciatale alla	Supply Vollage	17011		' (νυ – 3:3ν ± 0:3ν)						
				70V9089/79X6 Com'l Only			39/79X7 I Only	70V9089/79X9 Com'l & Ind			
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
lcc	Dynamic Operating Current (Parts Basta Astron)	nt Outputs Disabled	COM'L	S L	220 220	395 350	200 200	335 290	180 180	260 225	mA
	(Both Ports Active)	$f = f_{MAX}^{(1)}$	IND	S L					180 180	270 235	
ISB1	Standby Current (Both Ports - TTL		COM'L	S L	70 70	145 130	60 60	115 100	50 50	75 65	mA
	Level ilipuis)		IND	S L				_	50 50	85 75	
ISB2	Standby Current (One Port - TTL Level Inputs)	e Port - TTL $\overline{CE}_{B''} = V_{H}^{(3)}$	COM'L	S L	150 150	280 250	130 130	240 210	110 110	170 150	mA
	Level lilpuis)	Active Port Outputs Disabled, f=fmax ⁽¹⁾	IND	S L					110 110	180 160	
ISB3	Full Standby Current (Both Ports -	Both Ports CER and CEL > VDD - 0.2V VIN > VDD - 0.2V or	COM'L	S L	1.0 0.4	5 3	1.0 0.4	5 3	1.0 0.4	5 3	mA
ČMOS Level Inputs)	$VIN \ge VDD - 0.2V$ of $VIN \le 0.2V$, $f = 0^{(2)}$	IND	S L					1.0 0.4	5 3		
ISB4	(One Port -	Port - \overline{CE} "B" > V_{DD} - $0.2V^{(5)}$	COM'L	S L	140 140	270 240	120 120	230 200	100 100	160 140	mA
CMOS Level Inputs)	Inputs) $V_{\text{IN}} \ge \overline{V}_{\text{DD}} - 0.2V$ or $V_{\text{IN}} \le 0.2V$, Active Port Outputs Disabled, $f = f_{\text{MAX}}^{(1)}$	IND	S L					100 100	170 150		

- 3750 tbl 09a
- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. Icc pc(f=0) = 90mA (Typ).
- 5. $\overline{CE}x = V_{IL} \text{ means } \overline{CE}_{0X} = V_{IL} \text{ and } CE_{1X} = V_{IH}$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}0x = VIH \text{ or } CE1x = VIL$
 - $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{V}\text{DD}$ 0.2 V
 - $\overline{\text{CE}}$ x \geq V_{DD} 0.2V means $\overline{\text{CE}}$ 0x \geq V_{DD} 0.2V or CE1x \leq 0.2V
 - "X" represents "L" for left port or "R" for right port.
- 6. 'X' in part number indicates power rating (S or L).

^{1.} At VDD ≤ 2.0V input leakages are undefined.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾ (VDD = 3.3V ± 0.3V)(Cont'd)

	erature and					9/79X12 Only	70V9089 Com'l	9/79X15	u)
Symbol	Parameter	Test Condition	Version		Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
lcc	Dynamic Operating Current (Both Ports Active)	CEL and CER = VIL Outputs Disabled f = fMAX ⁽¹⁾	COM'L	S L	150 150	240 205	130 130	220 185	mA
	(BOII FOILS ACTIVE)	T = IMAX [*]	IND	S L					
ISB1	$ \begin{array}{ll} \text{Standby Current} \\ \text{(Both Ports - TTL} \\ \text{Level Inputs)} \end{array} $		COM'L	S L	40 40	65 50	30 30	55 35	mA
Level			IND	S L					
ISB2	Standby Current (One Port - TTL Level Inputs)	ort - TTL $\overline{CE}_{"B"} = V_{IH}^{(3)}$	COM'L	S L	100 100	160 140	90 90	150 130	mA
	Level IIIpuis)		IND	S L					
ISB3	Full Standby Current (Both Ports -	Both Ports CER and CEL > VDD - 0.2V	COM'L	S L	1.0 0.4	5 3	1.0 0.4	5 3	mA
	CMOS Level Inputs)	$V_{IN} \ge V_{DD} - 0.2V$ or $V_{IN} \le 0.2V$, $f = 0^{(2)}$	IND	S L					
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	$\begin{array}{l} \overline{\text{CE}}\text{"A"} \leq 0.2\text{V and} \\ \overline{\text{CE}}\text{"B"} \geq \text{VDD} - 0.2\text{V}^{(5)} \\ \text{Vin} \geq \overline{\text{VDD}} - 0.2\text{V or} \\ \text{Vin} \leq 0.2\text{V}, \text{ Active Port} \\ \text{Outputs Disabled, } f = \text{fMax}^{(1)} \end{array}$	COM'L	S L	90 90	150 130	80 80	140 120	mA
	TOWOS Level Inpuls)		IND	S L					

3750 tbl 09b

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. Icc Dc(f=0) = 90mA (Typ).
- 5. $\overline{CE}x = V_{IL} \text{ means } \overline{CE}_{0x} = V_{IL} \text{ and } CE_{1x} = V_{IH}$
 - $\overline{\text{CE}}$ x = ViH means $\overline{\text{CE}}$ 0x = ViH or CE1x = ViL
 - $\overline{\text{CE}}x \leq 0.2 \text{V}$ means $\overline{\text{CE}}_0x \leq 0.2 \text{V}$ and $\text{CE}_1x \geq \text{V}_{DD}$ 0.2 V
 - $\overline{\text{CE}}$ x \geq V_{DD} 0.2V means $\overline{\text{CE}}$ 0x \geq V_{DD} 0.2V or CE1x \leq 0.2V
 - "X" represents "L" for left port or "R" for right port.
- 6. 'X' in part number indicates power rating (S or L).

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

3750 tbl 10

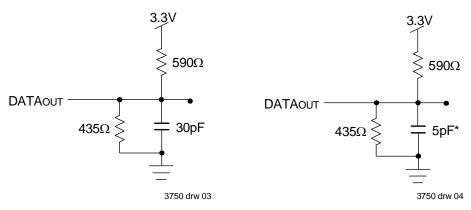


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tckLz, tckHz, toLz, and toHz).
*Including scope and jig.

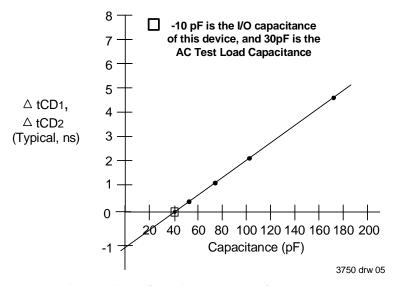


Figure 3. Typical Output Derating (Lumped Capacitive Load).

3750 tbl 11a

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3,4)}$ (VDD = 3.3V ± 0.3, TA = 0°C to +70°C)

Inouu	and Write Cycle Timing)(3,47)		89/79X6 I Only	70V90	89/79X7 I Only	70V9089/79X9 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19	_	22	_	25	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	10	_	12	_	15	_	ns
tCH1	Clock High Time (Flow-Through)(2)	6.5	_	7.5	_	12	_	ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	6.5	_	7.5	_	12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4	_	5	_	6	_	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	4	_	5	_	6	_	ns
tR	Clock Rise Time	_	3		3	_	3	ns
tF	Clock Fall Time	_	3		3	_	3	ns
tsa	Address Setup Time	3.5	_	4	_	4	_	ns
tha	Address Hold Time	0	_	0	_	1	_	ns
tsc	Chip Enable Setup Time	3.5	_	4	_	4	_	ns
thc	Chip Enable Hold Time	0	_	0	_	1	_	ns
tsw	R/W Setup Time	3.5	_	4	_	4	_	ns
tHW	R/W Hold Time	0	_	0	_	1	_	ns
tsp	Input Data Setup Time	3.5	_	4	_	4	_	ns
tHD	Input Data Hold Time	0	_	0	_	1	_	ns
tsad	ADS Setup Time	3.5	_	4	_	4	_	ns
tHAD	ADS Hold Time	0	_	0	_	1	_	ns
tscn	CNTEN Setup Time	3.5	_	4	_	4	_	ns
thcn	CNTEN Hold Time	0	_	0	_	1	_	ns
tsrst	CNTRST Setup Time	3.5	_	4	_	4	_	ns
tHRST	CNTRST Hold Time	0	_	0	_	1	_	ns
toE	Output Enable to Data Valid	_	6.5		7.5	_	9	ns
toLZ	Output Enable to Output Low-Z ⁽¹⁾	2		2		2		ns
tonz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾	_	15		18		20	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾	_	6.5	_	7.5	_	9	ns
toc	Data Output Hold After Clock High	2	_	2	_	2	_	ns
tckHZ	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	ns
Port-to-Port D	Delay	•	•	•		•		
tcwdd	Write Port Clock High to Read Data Delay	_	24		28	_	35	ns
tccs	Clock-to-Clock Setup Time	_	9	_	10	_	15	ns
	•		-	-	-	-	-	

Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
 This parameter is guaranteed by device characterization, but is not production tested.

^{2.} The Pipelined output parameters (tcyc2, tcb2) apply to either or both left and right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcb1) apply when FT/PIPE = VIL for that port.

^{3.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPE. FT/PIPE should be treated as a DC signal, i.e. steady state during operation.

^{4. &#}x27;X' in part number indicates power rating (S or L).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3,4)}$ (VDD = 3.3V ± 0.3, TA = 0°C to +70°C)(Cont'd)

	and write Cycle Timing)(8,47 (VDD = 3.3V ±		70V9089/79X12 Com'l Only		70V908979X15 Com'l Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	30		35		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	20		25		ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	12		12		ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	12		12		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	8		10		ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	8		10	_	ns
tr	Clock Rise Time	_	3	_	3	ns
tF	Clock Fall Time	_	3	_	3	ns
tsa	Address Setup Time	4		4	_	ns
tHA	Address Hold Time	1		1	_	ns
tsc	Chip Enable Setup Time	4		4	_	ns
thc	Chip Enable Hold Time	1		1		ns
tsw	R/W Setup Time	4		4		ns
thw	R/₩ Hold Time	1		1	_	ns
tsD	Input Data Setup Time	4		4	_	ns
thD	Input Data Hold Time	1		1	_	ns
tsad	ADS Setup Time	4	_	4	_	ns
thad	ADS Hold Time	1		1		ns
tscn	CNTEN Setup Time	4		4		ns
thcn	CNTEN Hold Time	1		1		ns
tsrst	CNTRST Setup Time	4	_	4	_	ns
tHRST	CNTRST Hold Time	1		1		ns
toe	Output Enable to Data Valid	_	12		15	ns
toLZ	Output Enable to Output Low-Z ⁽¹⁾	2		2	_	ns
tonz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through)(2)		25		30	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾	_	12		15	ns
toc	Data Output Hold After Clock High	2		2		ns
tckHz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2		2		ns
Port-to-Port I	Delay	•				
tcwdd	Write Port Clock High to Read Data Delay		40		50	ns
tccs	Clock-to-Clock Setup Time		15		20	ns

NOTES

3750 tbl 11b

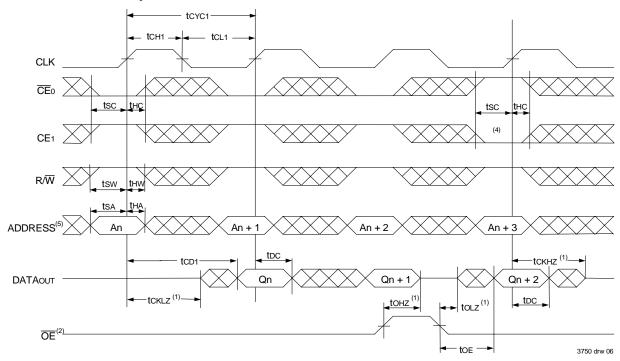
Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
 This parameter is guaranteed by device characterization, but is not production tested.

^{2.} The Pipelined output parameters (tcyc2, tcb2) apply to either or both left and right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcb1) apply when FT/PIPE = VIL for that port.

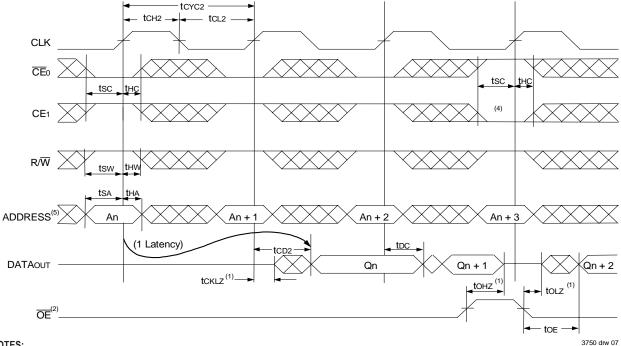
^{3.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPE. FT/PIPE should be treated as a DC signal, i.e. steady state during operation.

^{4. &#}x27;X' in part number indicates power rating (S or L).

Timing Waveform of Read Cycle for Flow-Through Output $(\overline{FT}/PIPE_{"X"} = VIL)^{(3,6)}$

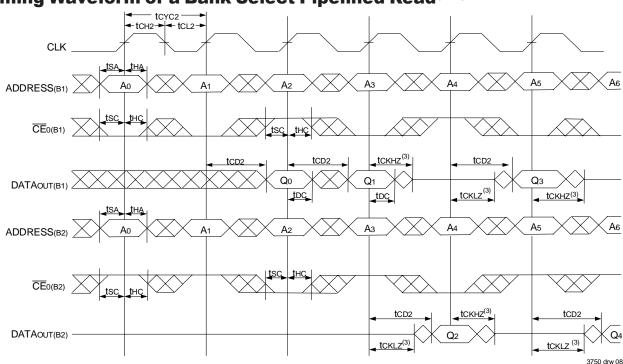


Timing Waveform of Read Cycle for Pipelined Output ($\overline{FT}/PIPE$ "x" = Vih)(3,6)

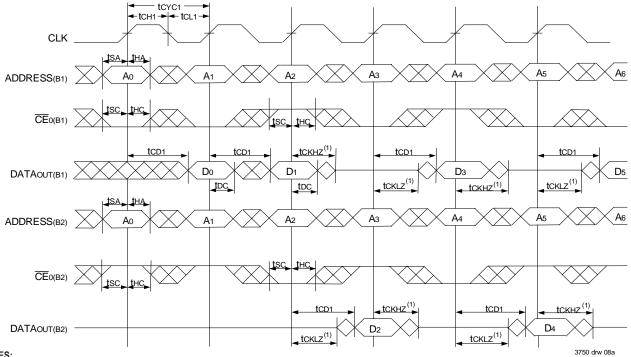


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = V_{IL}$, \overline{CNTEN} and $\overline{CNTRST} = V_{IH}$.
- 4. The output is disabled (High-impedance state) by $\overline{\text{CE}}_0$ = VIH or CE1 = VIL following the next rising edge of clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)

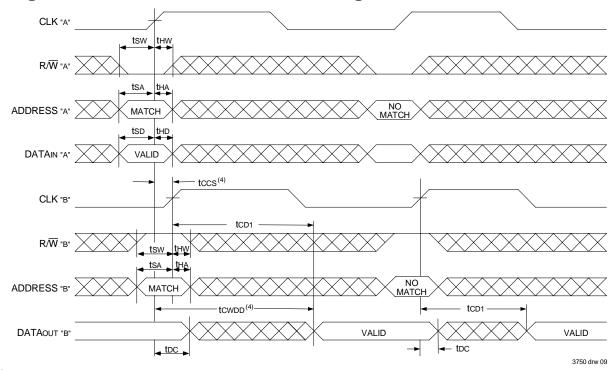


Timing Waveform of a Bank Select Flow-Through Read⁽⁶⁾



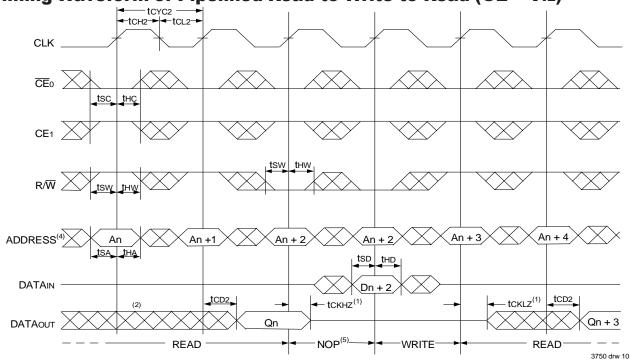
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9089/79 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{OE}}$ and $\overline{\text{ADS}}$ = VIL; $\overline{\text{CE1(B1)}}$, $\overline{\text{CE1(B2)}}$, $\overline{\text{R/W}}$, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = VIL; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.
- 5. \overline{OE} = V_{IL} for the Right Port, which is being read from. \overline{OE} = V_{IH} for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.

Timing Waveform Port-to-Port Flow-Through Read^(1,2,3,5)

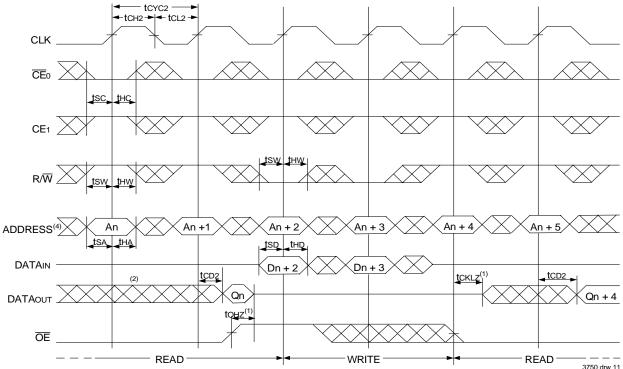


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. CEo and ADS = VIL; CE1, CNTEN, and CNTRST = VIH.
- 3. \overline{OE} = V_{IL} for the Port "B", which is being read from. \overline{OE} = V_{IH} for the Port "A", which is being written to.
- 4. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.
- 5. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = V_{IL}$)⁽³⁾

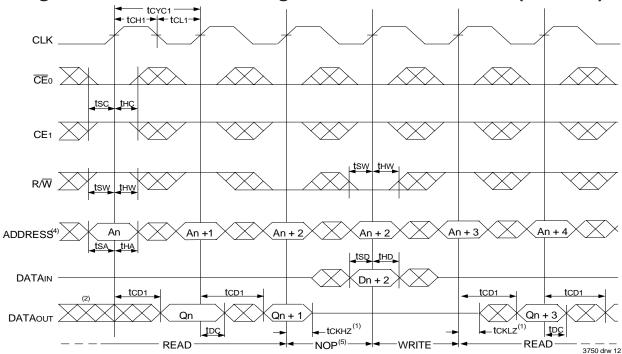


Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

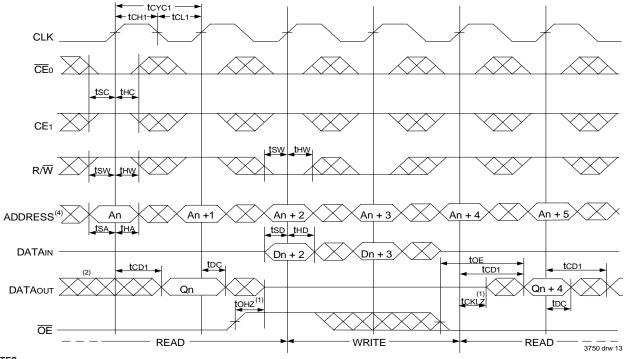


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = VIL; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = V_{IL}$)⁽³⁾

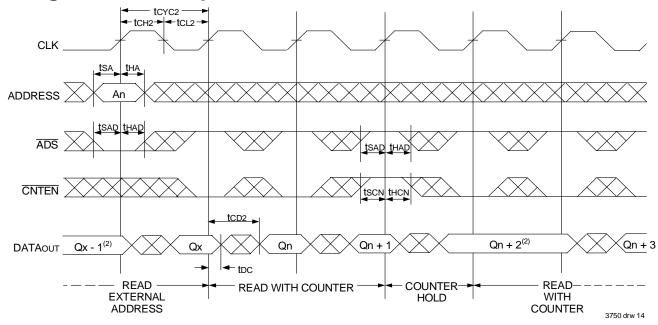


Timing Waveform of Flow-Through Read-to-Write-to-Read (OE Controlled)(3)

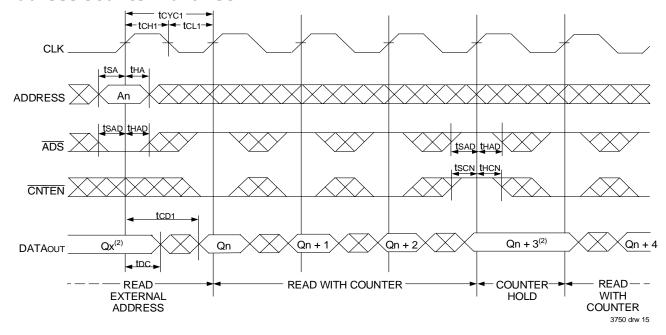


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = ViL; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = ViH.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

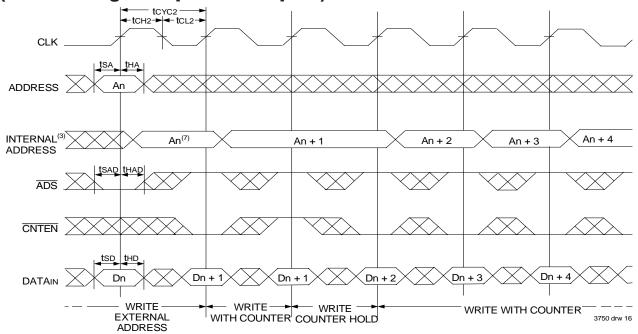


Timing Waveform of Flow-Through Counter Read with Address Counter Advance⁽¹⁾

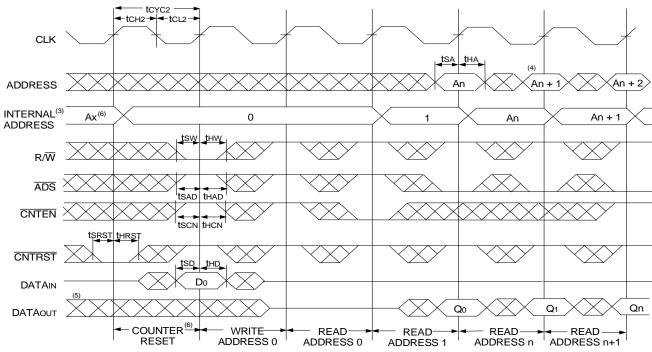


- 1. \overline{CE}_0 and \overline{OE} = V_{IL}; CE₁, R/ \overline{W} , and \overline{CNTRST} = V_{IH}.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



NOTES

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- 1. $\overline{CE_0}$ and R/W = VIL; CE1 and \overline{CNTRST} = VIH.
- $2 \overline{CF}_0 = V_{II} \cdot CF_1 = V_{IH}$
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = V_{IL} advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance.
 The 'An +1' address is written to during this cycle.

Functional Description

The IDT70V9089/79 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

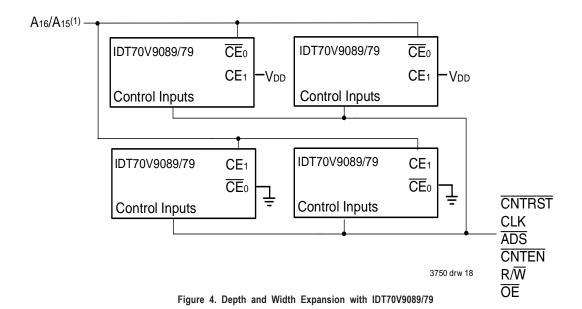
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the counter registers for fast interleaved memory applications.

A HIGH on $\overline{\text{CE}}_0$ or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9089/79's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0$ LOW and CE1 HIGH to re-activate the outputs.

Depth and Width Expansion

The IDT70V9089/79 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

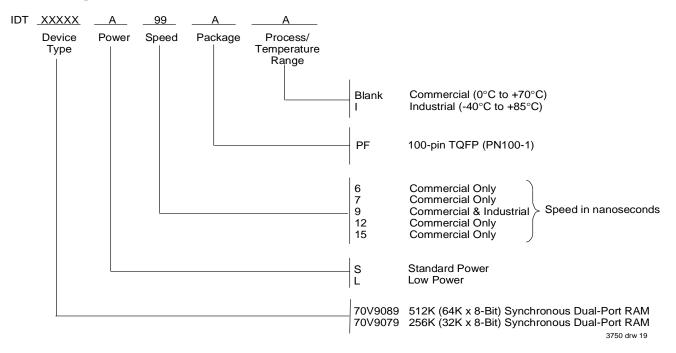
The IDT70V9089/79 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 16-bit or wider applications.



NOTE:

1. A₁₆ is for ID70V9089. A₁₅ is for ID70V9079.

Ordering Information



Ordering Information for Flow-through Devices

Old Flow-through Part	New Combined Part			
70V908S/L25	70V9089S/L12			
70V908S/L30	70V9089S/L15			

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Old Flow-through Part	New Combined Part			
70V908S/L25	70V9079S/L12			
70V908S/L30	70V9079S/L15			

3750 tbl 13

IDT Clock Solution for IDT70V9089/79 Dual-Port

IBT Glock Goldtion for IBT/CTCCCC/TC Back 1 Cit									
IDT Dual-Port Part Number	Dual-Port I/O Specitications		Clock Specifications			IDT	IDT		
	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement	Maximum Frequency	Jitter Tolerance	PLL Clock Device	Non-PLL Clock Device	
70V9089/79	3.3	LVTTL	9pF	40%	100	150ps	2305 2308 2309	49FCT3805 49FCT3805D/E 74FCT3807 74FCT3807D/E	

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Datasheet Document History

1/18/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections Added additional notes to pin configurations

Page 14 Added Depth and Width Expansion section.

6/11/99: Page 3 Deleted note 6 for Table II

11/12/99: Replaced IDT logo

3/31/00: Combined Pipelined 70V9089 family and Flow-through 70V908 family offerings into one data sheet

Changed ±200mV in waveform notes to 0mV

Added corresponding part chart with ordering information

1/10/01: Page 3 Changed information in Truth Table II

Page 4 Increased storage temperature parameters

Clarified TA parameter

Page 5 DC Electrical parameters-changed wording from "open" to "disabled"

Removed Preliminary Status

01/15/04: Consolidated multiple devices into one datasheet

Changed naming conventions from Vcc to Vdd and from GND to Vss

Removed I-temp footnote from tables

Page 2 Added date revision to pin configuration

Page 4 Added Junction Temperature to Absolute Maximum Ratings Table

Added Ambient Temperature footnote

Page 5 Added I-temp numbers for 9ns speed to the DC Electrical Characteristics Table

Added 6ns & 7ns speeds DC power numbers to the DC Electrical Characteristics Table

Page 7 Added I-temp for 9ns speed to AC Electrical Characteristics Table

Added 6ns & 7ns speeds AC timing numbers to the AC Electrical Characteristics Table

Page 16 Added 6ns & 7ns speeds grade and 9ns I-temp to ordering information

Added IDT Clock Solution Table

Page 1 & 17 Replaced ® IDT logo with ™ new logo

05/11/04: Page 1 & 19 Added 7ns speed grade to ordering information

Page 5 Added 7ns speed DC power numbers to the DC Electrical Characteristics Table

Page 8 Added 7ns speed AC timing numbers to the AC Electrical Characteristics Table